

Description

The ESD4V5PD is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low surge clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The ESD4V5PD complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small 1.6x1.0x0.5mm lead-free DFN package. The small size and high ESD surge protection make ESD4V5PD an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Ultra small package: 1.6x1.0x0.5mm
- Protects one data or power line
- Working voltage: 4.5V
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 135A (8/20ns)
- RoHS Compliant

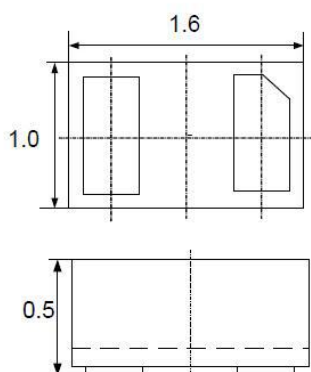
Mechanical Characteristics

- Package: DFN1610-2 (1.6x1.0x0.5mm)
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

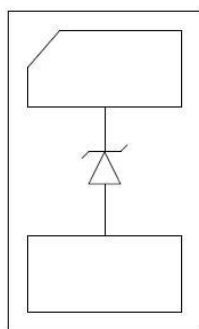
Applications

- Mobile Phones
- Battery Protection
- Power Line Protection
- Vbat pin for Mobile Devices
- Hand Held Portable Applications

Dimensions & Symbol (Unit: mm Max)



Package Dimensions



Circuit and Pin Schematic

Ordering Information

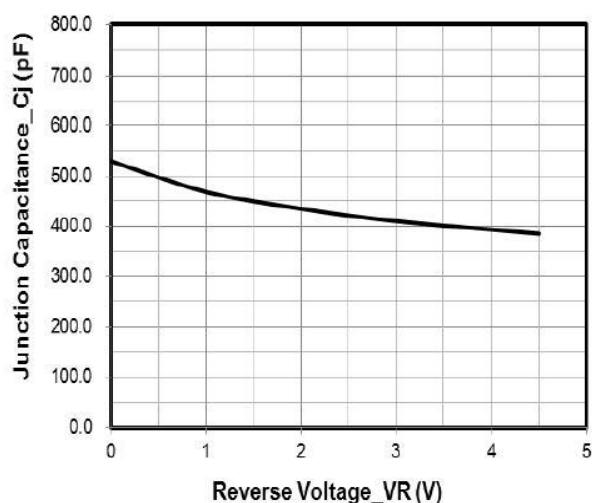
Part Number	Packaging	Reel Size
ESD4V5PD	3000/Tape & Reel	7 inch

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P _{ppp}	2500	W
Peak Pulse Current (8/20μs)	I _{pp}	135	A
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

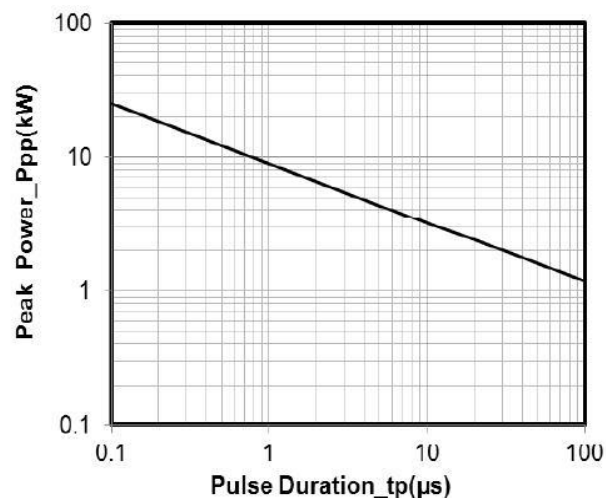
Electrical Characteristics (T_A=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			4.5	V	
Breakdown Voltage	V _{BR}	4.8			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	uA	V _{RWM} = 4.5V
Clamping Voltage	V _C			7	V	I _{PP} = 10A (8 x 20μs pulse)
Clamping Voltage	V _C			18	V	I _{PP} = 135A (8 x 20μs pulse)
Junction Capacitance	C _J			750	pF	V _R = 0V, f = 1MHz

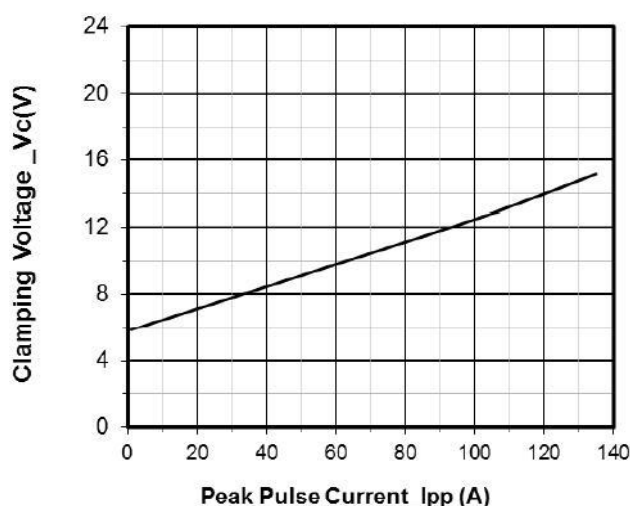
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



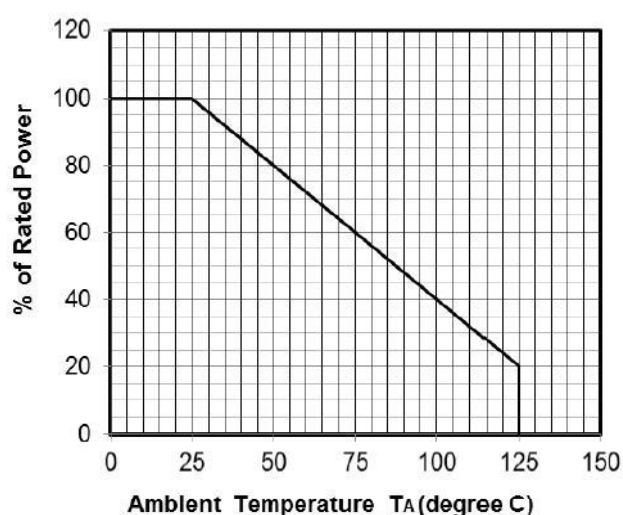
Junction Capacitance vs. Reverse Voltage



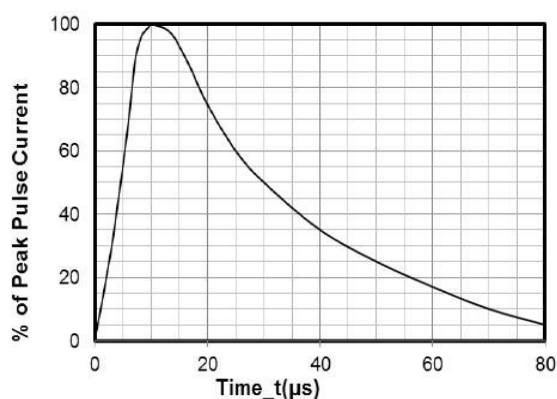
Peak Pulse Power vs. Pulse Time



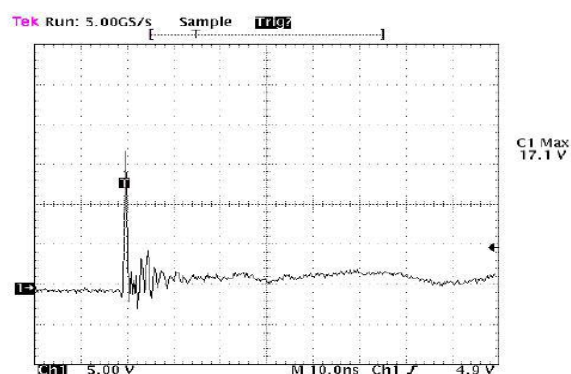
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20 μs Pulse Waveform



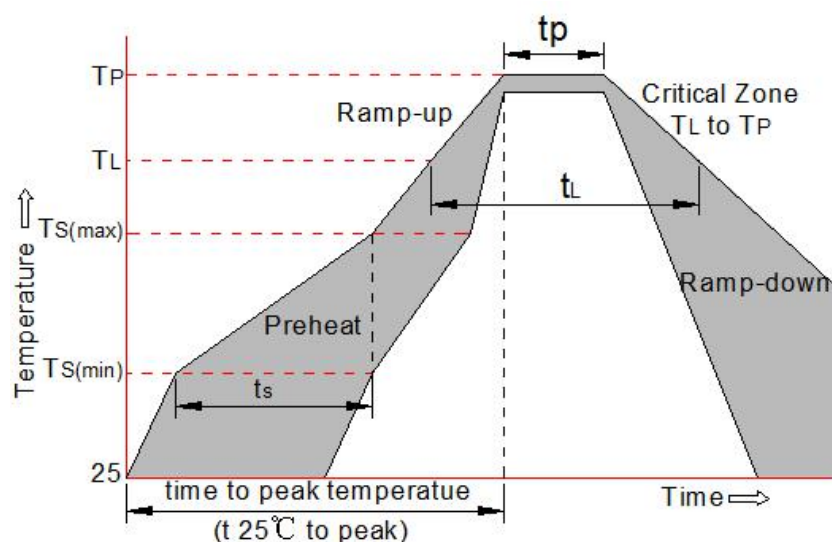
Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

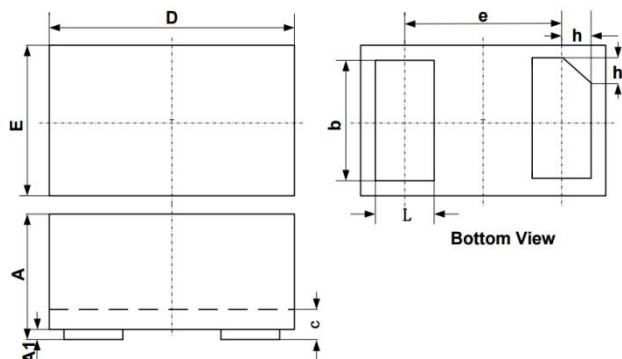
+8 kV Contact per IEC61000-4-2

Soldering Parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

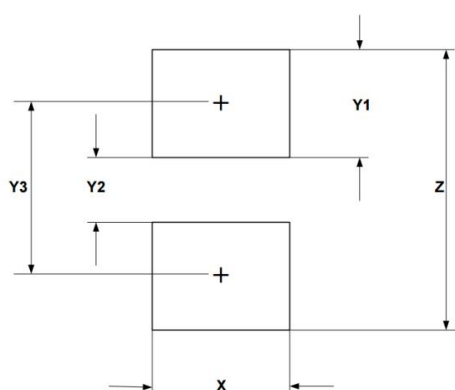


Package Mechanical Data



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.75	0.80	0.85	0.030	0.032	0.034
c	0.10	0.15	0.20	0.004	0.006	0.007
D	1.55	1.60	1.65	0.062	0.064	0.066
e	1.10 BSC			0.044 BSC		
E	0.95	1.00	1.05	0.038	0.040	0.042
L	0.35	0.40	0.45	0.014	0.016	0.018
h	0.15	0.20	0.25	0.006	0.008	0.010

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	1.00	0.040
Y1	0.62	0.025
Y2	0.60	0.024
Y3	1.22	0.049
Z	1.85	0.074